

# Tarek Hidouri

## List of Publications by Year in descending order

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28  
papers

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citations

1040056

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1125743

13  
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29  
all docs

29  
docs citations

29  
times ranked

131  
citing authors

#	ARTICLE	IF	CITATIONS
1	LSE investigation of the thermal effect on band gap energy and thermodynamic parameters of BInGaAs/GaAs Single Quantum Well. <i>Optical Materials</i> , 2016, 62, 267-272.	3.6	25
2	Localized state exciton model investigation of B-content effect on optical properties of BGaAs/GaAs epilayers grown by MOCVD. <i>Vacuum</i> , 2016, 132, 10-15.	3.5	18
3	Impact of photoluminescence temperature and growth parameter on the exciton localized in B x Ga 1-x As/GaAs epilayers grown by MOCVD. <i>Optical Materials</i> , 2016, 60, 487-494.	3.6	18
4	Detecting Spatially Localized Exciton in Self-Organized InAs/InGaAs Quantum Dot Superlattices: a Way to Improve the Photovoltaic Efficiency. <i>Nanoscale Research Letters</i> , 2017, 12, 450.	5.7	14
5	Effect of etching time and illumination on optical properties of SiNWs elaborated by Metal Assisted Chemical Etching (MACE) for organic photovoltaic applications. <i>Superlattices and Microstructures</i> , 2015, 85, 925-930.	3.1	12
6	Carrierâ€™ localization and thermal redistribution in InAlAs/InP grown by MOCVD on (311)A- and (311)B-InP substrates. <i>Applied Physics A: Materials Science and Processing</i> , 2019, 125, 1.	2.3	12
7	Engineering of carrier localization in BGaAs SQW for novel intermediate band solar cells: Thermal annealing effect. <i>Solar Energy</i> , 2020, 199, 183-191.	6.1	12
8	Investigation of the localization phenomenon in quaternary BInGaAs/GaAs for optoelectronic applications. <i>Superlattices and Microstructures</i> , 2017, 103, 386-394.	3.1	10
9	Structural, electronic and optical properties of M-doped anatase TiO <sub>2</sub> (M= Fe or Au): A first principle investigation. <i>Computational Condensed Matter</i> , 2021, 28, e00576.	2.1	10
10	Effect of carriers localized in clusters on optical properties of In <sub>0.21</sub> Ga <sub>0.79</sub> As/GaAs multiple quantum wells. <i>Current Applied Physics</i> , 2017, 17, 1-5.	2.4	9
11	Carrier localization in In <sub>0.21</sub> Ga <sub>0.79</sub> As/GaAs multiple quantum wells: A modified PÃssler model for the S-shaped temperature dependence of photoluminescence energy. <i>Superlattices and Microstructures</i> , 2017, 102, 351-358.	3.1	8
12	Impact of localization phenomenon and temperature on the photoluminescence spectra of GaSbBi alloys and GaSbBi/GaAs quantum dots. <i>Superlattices and Microstructures</i> , 2019, 129, 252-258.	3.1	8
13	BGaAs strain compensation layer in novel BGaAs/InGaAs/BGaAs heterostructure: Exceptional tunability. <i>Applied Surface Science</i> , 2020, 524, 146573.	6.1	7
14	Investigation of novel titanate nanotubes modified with Ce, Fe, Zn and Zr for efficient dye degradation performance, inhibition of bacterial and fungal growth and anticorrosion activity in acid medium. <i>Reaction Kinetics, Mechanisms and Catalysis</i> , 2021, 134, 517-537.	1.7	7
15	Ge/GaAs Based Negative Capacitance Tunnel FET Biosensor: Proposal and Sensitivity Analysis. <i>Silicon</i> , 2022, 14, 10475-10483.	3.3	7
16	Effect of wavelengths and excitation density on the optical properties of P3HT: SiNWs bulk heterojunction for photovoltaic applications. <i>Superlattices and Microstructures</i> , 2016, 97, 409-416.	3.1	6
17	New investigation of electronic properties of BGaAs/GaAs single quantum well for photonic applications. <i>Optik</i> , 2020, 205, 164253.	2.9	6
18	Performance Analysis of III-V and IV Semiconductors Based Double Gate Hetero Material Negative Capacitance TFET. <i>Silicon</i> , 2022, 14, 8529-8541.	3.3	5

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19	Combined impact of B <sub>2</sub> H <sub>6</sub> flow and growth temperature on morphological, structural, optical, and electrical properties of MOCVD-grown B(In)GaAs heterostructures designed for optoelectronics. Applied Surface Science, 2022, 577, 151884.	6.1	4
20	Tailoring the electronic, optical and mechanical properties of KMgH <sub>3</sub> and RbCaH <sub>3</sub> perovskite hydrides without and with Samarium. Journal of Solid State Chemistry, 2022, 309, 122952.	2.9	4
21	Experimental and theoretical study of novel BGaAs/GaAs single quantum well for photonic applications. Vacuum, 2020, 173, 109182.	3.5	3
22	Graphene induced weak carrier localization in InGaN nanorods directly grown on graphene-covered Si. Diamond and Related Materials, 2020, 106, 107841.	3.9	3
23	Tuning spontaneous emission in BInGaAs/GaAs QWs by varying the growth temperature: above 1.2 μm emission and solar cells application. Optical and Quantum Electronics, 2021, 53, 1.	3.3	3
24	Point defect localization and cathodoluminescence emission in undoped μ-Ga <sub>2</sub> O <sub>3</sub> . Journal Physics D: Applied Physics, 2022, 55, 295103.	2.8	3
25	New Strategy against COVID-19: L-Serine Doped QDs for Fast Detection of COVID-19 and Blocking of S-Protein. ECS Journal of Solid State Science and Technology, 2020, 9, 106002.	1.8	2
26	Effect of Polymer Capping Layer on III-V Materials: Disorder's Control in P3HT/BGaAs/GaAs Heterostructure. Journal of Electronic Materials, 0, , 1.	2.2	1
27	Growth temperature impact on MOVPE-grown BInGaAs/GaAs QWs designed for optoelectronic applications. Journal of Materials Science: Materials in Electronics, 2021, 32, 20115-20129.	2.2	0
28	Transfer mechanisms and geometry effect on the dynamics of excitons in boron-containing GaAs alloys: Time-resolved photoluminescence investigation. Optical Materials, 2021, 119, 111386.	3.6	0